

27LV256

256K (32K x 8) Low-Voltage CMOS EPROM

FEATURES

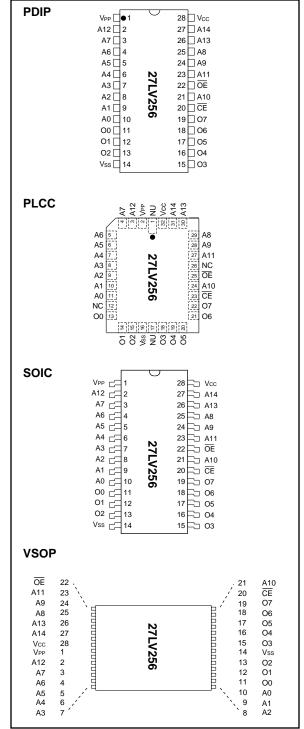
- Wide voltage range 3.0V to 5.5V
- High speed performance
- 200 ns access time available at 3.0V
- CMOS Technology for low power consumption
 - 8 mA Active current at 3.0V
 - 20 mA Active current at 5.5V
 - 100 µA Standby current
- · Factory programming available
- Auto-insertion-compatible plastic packages
- · Auto ID aids automated programming
- · Separate chip enable and output enable controls
- High speed "Express" programming algorithm
- Organized 32K x 8: JEDEC standard pinouts
 - 28-pin Dual-in-line package
 - 32-pin PLCC package
 - 28-pin SOIC package
 - 28-pin VSOP package
 - Tape and reel
- Data Retention > 200 years
- Available for the following temperature ranges:
 - Commercial: 0°C to +70°C
 - Industrial: -40°C to +85°C

DESCRIPTION

The Microchip Technology Inc. 27LV256 is a low voltage (3.0 volt) CMOS EPROM designed for battery powered applications. The device is organized as a 32K x 8 (32K-Byte) non-volatile memory product. The 27LV256 consumes only 8 mA maximum of active current during a 3.0 volt read operation therefore improving battery performance. This device is designed for very low voltage applications where conventional 5.0 volt only EPROMS can not be used. Accessing individual bytes from an address transition or from power-up (chip enable pin going low) is accomplished in less than 200 ns at 3.0V. This device allows systems designers the ability to use low voltage non-volatile memory with today's' low voltage microprocessors and peripherals in battery powered applications.

A complete family of packages is offered to provide the most flexibility in applications. For surface mount applications, PLCC, VSOP or SOIC packaging is available. Tape and reel packaging is also available for PLCC or SOIC packages.

PACKAGE TYPES



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1.0 ELECTRICAL CHARACTERISTICS

1.1 <u>Maximum Ratings*</u>

Vcc and input voltages w.r.t. Vss0.6V to +7.25V
VPP voltage w.r.t. VSS during programming0.6V to +14V
Voltage on A9 w.r.t. Vss0.6V to +13.5V
Output voltage w.r.t. Vss0.6V to Vcc +1.0V
Storage temperature65°C to +150°C
Ambient temp. with power applied65°C to +125°C
*Notice: Stresses above those listed under "Maximum Ratings" may cause permanent damage to the device. This is a stress rat-

may cause permanent damage to the device. This is a stress rating only and functional operation of the device at those or any other conditions above those indicated in the operation listings of this specification is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability.

TABLE 1-1: PIN FUNCTION TABLE

Name	Function
A0-A14	Address Inputs
CE	Chip Enable
ŌĒ	Output Enable
Vpp	Programming Voltage
00 - 07	Data Output
Vcc	+5V or +3V Power Supply
Vss	Ground
NC	No Connection; No Internal Connection
NU	Not Used; No External Connection Is Allowed

TABLE 1-2: READ OPERATION DC CHARACTERISTICS

			Com	= +5V nmercia istrial:	±10% or 3.0\ al:	indicated = 0°C to +70°C = -40°C to +85°C	
Parameter	Part*	Status	Symbol	Min.	Max.	Units	Conditions
Input Voltages	all	Logic "1" Logic "0"	Vih Vil	2.0 -0.5	Vcc+1 0.8	V V	
Input Leakage	all		ΙLI	-10	10	μΑ	VIN = 0 to VCC
Output Voltages	all	Logic "1" Logic "0"	Voh Vol	2.4	0.45	V V	IOH = -400 μA IOL = 2.1 mA
Output Leakage	all		Ilo	-10	10	μΑ	VOUT = 0V to VCC
Input Capacitance	all	_	CIN	—	6	pF	VIN = 0V; Tamb = 25°C; f = 1 MHz
Output Capacitance	all	—	Соит	—	12	pF	Vout = 0V; Tamb = 25°C; f = 1 MHz
Power Supply Current, Active	С	TTL input	ICC1	_	20 @ 5.0V 8 @ 3.0V	mA mA	VCC = 5.5V; VPP = VCC f = 1 MHz;
		TTL input	ICC2		25 @ 5.0V 10 @ 3.0V	mA mA	$\overline{OE} = \overline{CE} = VIL;$ $IOUT = 0 mA;$ $VIL = -0.1 to 0.8V;$ $VIH = 2.0 to VCC;$ Note 1
Power Supply Current, Standby	C I all	TTL input TTL input CMOS input	lcc(s)	_	1 @ 3.0V 2 @ 3.0V 100 @ 3.0V	mA mA μA	$\overline{CE}=Vcc \pm 0.2V$

* Parts: C=Commercial Temperature Range

I =Industrial Temperature Ranges

Note 1: Typical active current increases .75 mA per MHz up to operating frequency for all temperature ranges.

TABLE 1-3: READ OPERATION AC CHARACTERISTICS

AC Testing Waveform:VIH = 2.4V and VIL = 0.45V; VOH = 2.0V VOL = 0.8VOutput Load:1 TTL Load + 100 pFInput Rise and Fall Times:10 nsAmbient Temperature:Commercial:Tamb = 0°C to +70°CIndustrial:Tamb = -40°C to +85°C										
Demonster	0	27HC	256-20	27HC	7HC256-25 27		27HC256-30		O an all the me	
Parameter	Sym	Min	Max	Min	Max	Min	Max	Units	Conditions	
Address to Output Delay	tACC	_	200		250		300	ns	$\overline{CE} = \overline{OE} = VIL$	
CE to Output Delay	tCE	_	200		250		300	ns	OE = VIL	
OE to Output Delay	tOE		100	—	125	—	125	ns	CE = VIL	
CE or OE to O/P High Impedance	tOFF	0	50	0	50	0	50	ns		
Output Hold from Address CE or OE, whichever goes first	tOH	0		0		0		ns		

FIGURE 1-1: READ WAVEFORMS

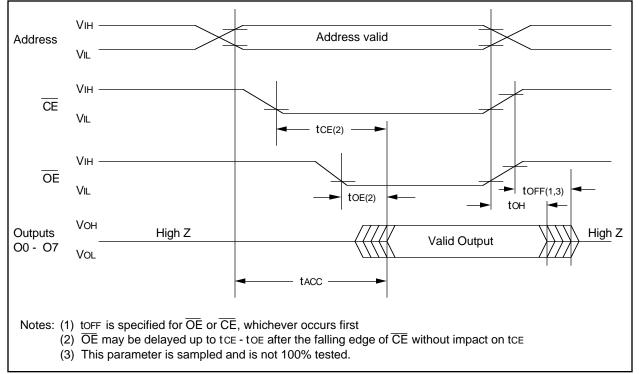


TABLE 1-4: PROGRAMMING DC CHARACTERISTICS

	Ambient Temperature: Tamb = $25^{\circ}C \pm 5^{\circ}C$ Vcc = $6.5V \pm 0.25V$, VPP = $13.0V \pm 0.25V$							
Parameter	Status	Symbol	Min	Max.	Units	Conditions		
Input Voltages	Logic"1" Logic"0"	Vih Vil	2.0 -0.1	Vcc+1 0.8	V V			
Input Leakage	—	IЦ	-10	10	μA	VIN = 0V to VCC		
Output Voltages	Logic"1" Logic"0"	Vон Vol	2.4	0.45	V V	IOH = -400 μA IOL = 2.1 mA		
Vcc Current, program & verify	—	ICC2	_	20	mA	Note 1		
VPP Current, program	—	IPP2	_	25	mA	Note 1		
A9 Product Identification		Vн	11.5	12.5	V			

Note 1: VCC must be applied simultaneously or before VPP and removed simultaneously or after VPP.

TABLE 1-5: PROGRAMMING AC CHARACTERISTICS

for Program, Program Verify and Program Inhibit ModesAC Testing Waveform: Output Load:VIH=2.4V and VIL=0.45V; VOH=2.0V; VOL=0.8V 1 TLL Load + 100pF Ambient Temperature:Ambient Temperature:Tamb=25°C±5°C VCC= 6.5V ± 0.25V, VPP = 13.0V ± 0.25V									
Parameter		Symbol	Min.	Max.	Units	Remarks			
Address Set-Up Time		tAS	2	_	μs				
Data Set-Up Time		tDS	2	—	μs				
Data Hold Time		tDH	2	—	μs				
Address Hold Time		tAH	0	_	μs				
Float Delay (2)		tDF	0	130	ns				
Vcc Set-Up Time		tvcs	2	_	μs				
Program Pulse Width (1)		tPW	95	105	μs	100 μs typical			
CE Set-Up Time		tCES	2	_	μs				
OE Set-Up Time		tOES	2	—	μs				
VPP Set-Up Time		tVPS	2	—	μs				
Data Valid from OE		tOE		100	ns				

Note 1: For express algorithm, initial programming width tolerance is 100 μs $\pm 5\%.$

2: This parameter is only sampled and not 100% tested. Output float is defined as the point where data is no longer driven (see timing diagram).

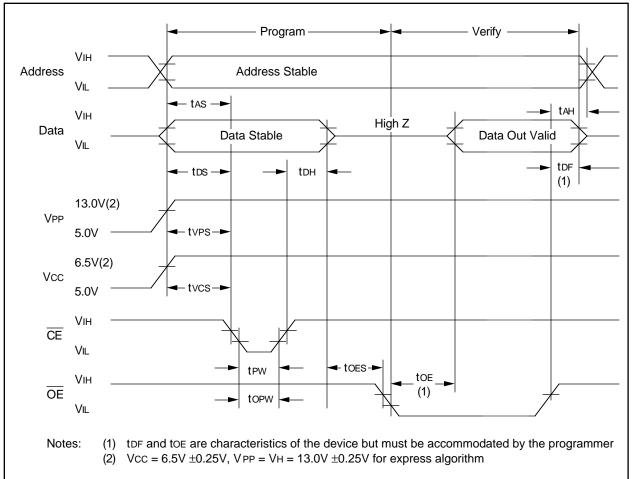


FIGURE 1-2:	PROGRAMMING WAVEFORMS
FIGURE 1-2:	

Operation Mode	CE	ŌĒ	VPP	A9	00 - 07
Read	VIL	VIL	Vcc	Х	Dout
Program	VIL	Viн	Vн	Х	Din
Program Verify	Viн	VIL	Vн	Х	Dout
Program Inhibit	Viн	Viн	Vн	Х	High Z
Standby	Viн	Х	Vcc	Х	High Z
Output Disable	VIL	Viн	Vcc	Х	High Z
Identity	VIL	VIL	Vcc	Vн	Identity Code

TABLE 1-6: MODES

X = Don't Care

1.2 <u>Read Mode</u>

(See Timing Diagrams and AC Characteristics)

Read Mode is accessed when:

- a) the \overline{CE} pin is low to power up (enable) the chip
- b) the $\overline{\text{OE}}$ pin is low to gate the data to the output pins

For Read operations, if the addresses are stable, the address access time (tACC) is equal to the delay from \overline{CE} to output (tCE). Data is transferred to the output after a delay from the falling edge of \overline{OE} (tOE).

1.3 Standby Mode

The standby mode is defined when the $\overline{\text{CE}}$ pin is high (VIH) and a program mode is not defined. Output Disable

1.4 Output Enable

This feature eliminates bus contention in multiple bus microprocessor systems and the outputs go to a high impedance when the following condition is true:

• The OE pin is high and program mode is not defined.

1.5 Programming Mode

The Express algorithm has been developed to improve on the programming throughput times in a production environment. Up to 10 100-microsecond pulses are applied until the byte is verified. No over-programming is required. A flowchart of the express algorithm is shown in Figure 1.

Programming takes place when:

- a) Vcc is brought to the proper voltage
- b) VPP is brought to the proper VH level
- c) the OE pin is high
- d) the CE pin is low

Since the erased state is "1" in the array, programming of "0" is required. The address to be programmed is set via pins A0-A14 and the data to be programmed is presented to pins O0-O7. When data and address are stable, a low-going pulse on the \overline{CE} line programs that location.

1.6 <u>Verify</u>

After the array has been programmed it must be verified to ensure that all the bits have been correctly programmed. This mode is entered when all of the following conditions are met:

- a) Vcc is at the proper level
- b) VPP is at the proper VH level
- c) the \overline{CE} pin is high
- d) the OE line is low

1.7 Inhibit

When Programming multiple devices in parallel with different data, only \overline{CE} needs to be under separate control to each device. By pulsing the \overline{CE} line low on a particular device, that device will be programmed, and all other devices with \overline{CE} held high will not be programmed with the data although address and data are available on their input pins.

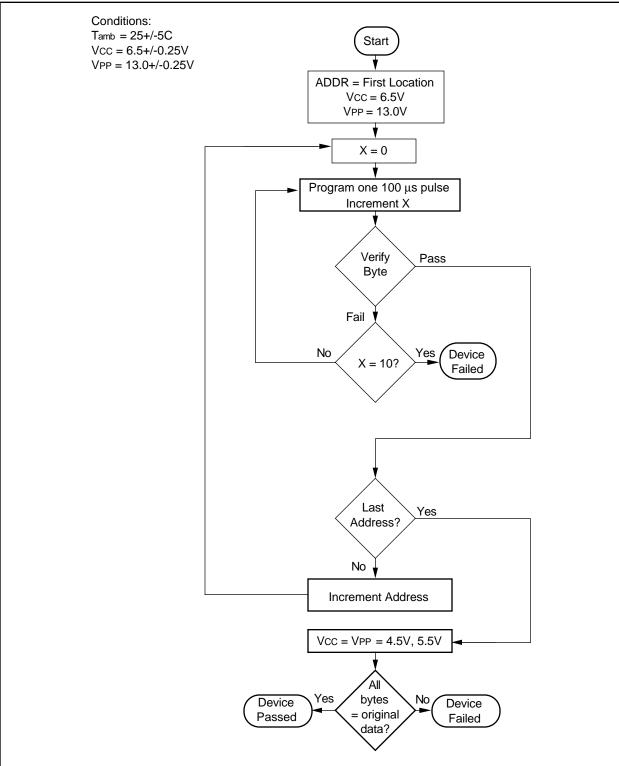
1.8 Identity Mode

In this mode specific data is outputted which identifies the manufacturer as Microchip Technology Inc. and device type. This mode is entered when Pin A9 is taken to VH (11.5V to 12.5V). The \overline{CE} and \overline{OE} lines must be at VIL. A0 is used to access any of the two non-erasable bytes whose data appears on O0 through O7.

Pin 🔶	Input	Output								
Identity	A0	0	0	0	0	0	0	0	0	Н
Identity		7	6	5	4	3	2	1	0	е
										Х
Manufacturer	VIL	0	0	1	0	1	0	0	1	29
Device Type*	Vін	1	0	0	0	1	1	0	0	8C

* Code subject to change.





27LV256

NOTES:

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27LV256

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27LV256 Product Identification System

To order or to obtain information, e.g., on pricing or delivery, please use the listed part numbers, and refer to the factory or the listed sales offices.

27L\	V256 – 25	I /P				
			Package:	L	=	Plastic Leaded Chip Carrier
			-	Р	=	Plastic DIP (600 Mil)
						Plastic SOIC (300 Mil)
				VS	=	Very Small Outline Package (VSOP) 8X13.4mm
			Temperature	Blank	=	0°C to +70°C
			Range:	Ι	=	-40°C to +85°C
			Access	20	=	200 ns
			Time:	25	=	250 ns
				30	=	300 ns (SOIC only)
			Device:	27LV256		256K (32K x 8) Low-Voltage CMOS EPROM

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